



**80V 3.2mΩ N-Ch Power MOSFET**

**Features**

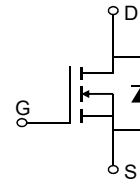
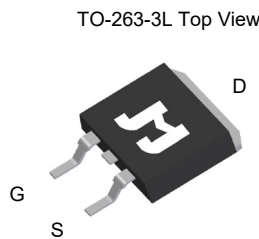
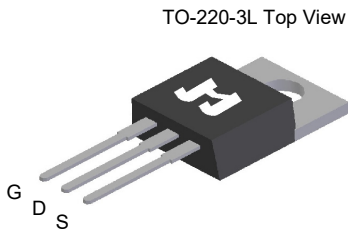
- Ultra-low  $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100%  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

**Product Summary**

Parameter	Value	Unit
$V_{DS}$	80	V
$V_{GS(th)}_{Typ}$	3.0	V
$I_D$ (@ $V_{GS} = 10V$ ) <sup>(1)</sup>	160	A
$R_{DS(ON)}_{Typ}$ (@ $V_{GS} = 10V$ )	3.2	mΩ

**Applications**

- Motor Driving in Power Tool, E-vehicle, Robotics
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Power Management in Telecom., Industrial Automation, CE

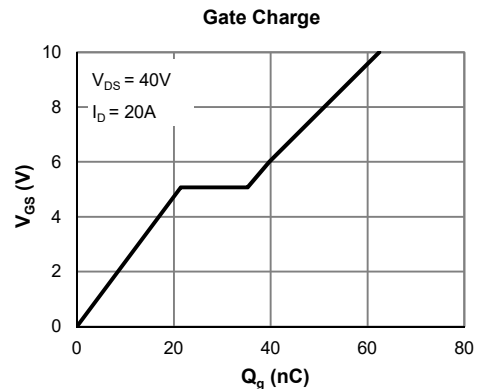
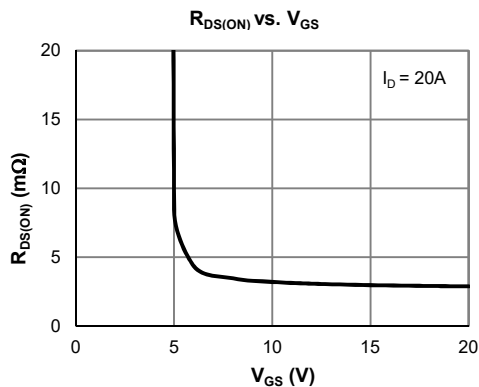


**Ordering Information**

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSH0804NC-U	TO-220-3L	3	SH0804N	NA	-55 to 150	Tube	50
JMSH0804NE-13	TO-263-3L	3	SH0804N	1	-55 to 150	13-inch Reel	800

**Absolute Maximum Ratings** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	80	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>(1)</sup>	$I_D$	$T_C = 25^\circ\text{C}$	160
		$T_C = 100^\circ\text{C}$	100
Pulsed Drain Current <sup>(2)</sup>	$I_{DM}$	519	A
Avalanche Energy <sup>(3)</sup>	$E_{AS}$	434	mJ
Power Dissipation <sup>(4)</sup>	$P_D$	$T_C = 25^\circ\text{C}$	192
		$T_C = 100^\circ\text{C}$	76
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C





**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
<b>STATIC PARAMETERS</b>							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	80	90		V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 64\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	$\mu\text{A}$	
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0	3.0	4.0	V	
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	TO-263-3L		3.2	4.0	m $\Omega$
			TO-220-3L		3.4	4.2	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		43		S	
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.70	1.0	V	
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			160	A	

**DYNAMIC PARAMETERS** <sup>(5)</sup>

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 40\text{V}, f = 1\text{MHz}$		4083		pF
Output Capacitance	$C_{oss}$			1313		pF
Reverse Transfer Capacitance	$C_{rss}$			42		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		1.5		$\Omega$

**SWITCHING PARAMETERS** <sup>(5)</sup>

Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 40\text{V}, I_D = 20\text{A}$		62		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$ )	$Q_g$			40		nC
Gate Source Charge	$Q_{gs}$			21		nC
Gate Drain Charge	$Q_{gd}$			13.8		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 40\text{V}$ $R_L = 2.0\Omega, R_{GEN} = 3\Omega$		18.9		ns
Turn-On Rise Time	$t_r$			28		ns
Turn-Off DelayTime	$t_{D(off)}$			38		ns
Turn-Off Fall Time	$t_f$			13.1		ns
Body Diode Reverse Recovery Time	$t_{rr}$		$I_F = 20\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$		57	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 20\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$		85		nC

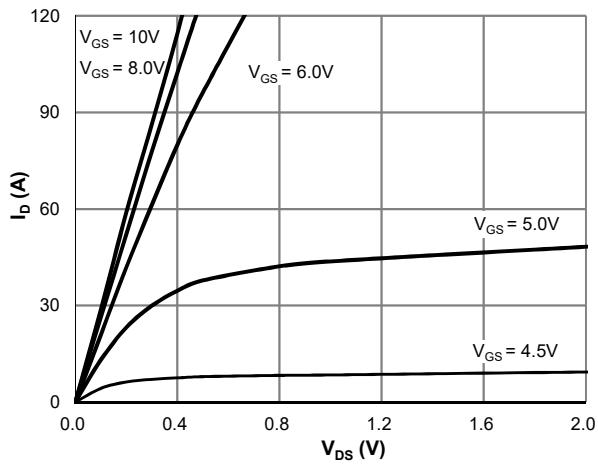
**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45	55	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.65	0.80	$^\circ\text{C}/\text{W}$

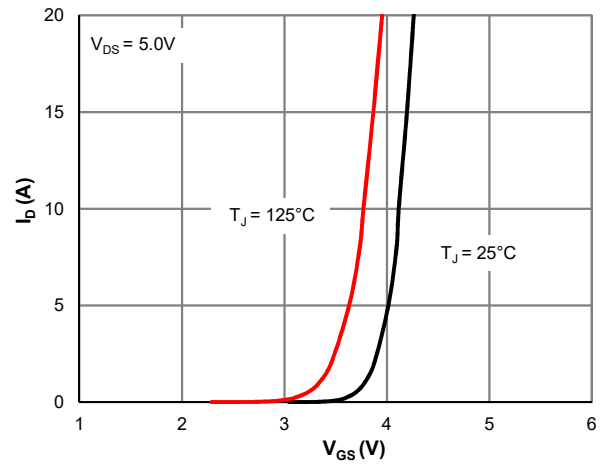
**Notes:**

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under  $T_{J\_Max} = 150^\circ\text{C}$ .
3.  $E_{AS}$  of 434 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.0\text{mH}$ ,  $I_{AS} = 17\text{A}$ ,  $V_{GS} = 10\text{V}$ ,  $V_{DD} = 40\text{V}$ ; 100% test at  $L = 0.1\text{mH}$ ,  $I_{AS} = 68\text{A}$ .
4. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 150^\circ\text{C}$ .
5. This value is guaranteed by design hence it is not included in the production test.

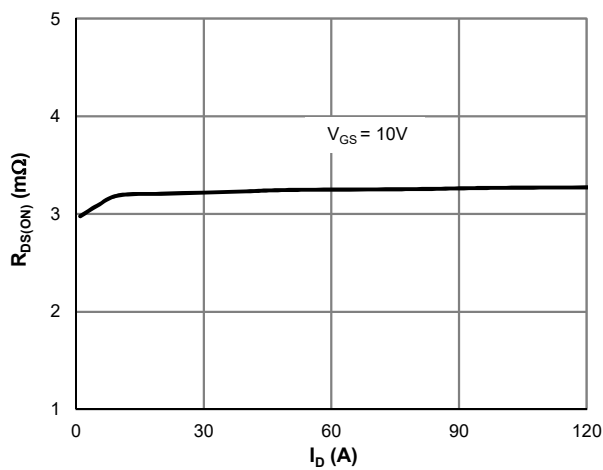
**Typical Electrical & Thermal Characteristics**



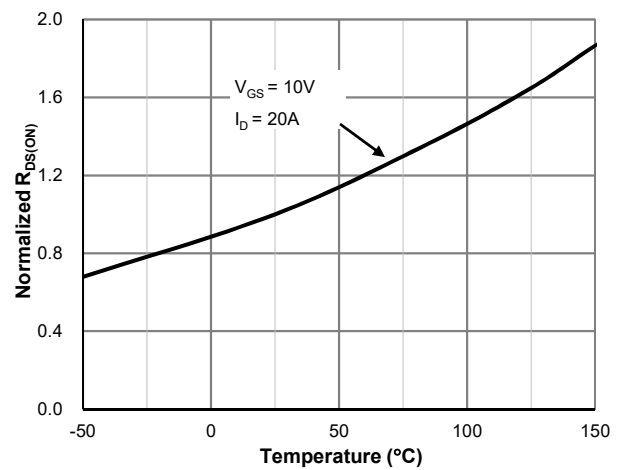
**Figure 1: Saturation Characteristics**



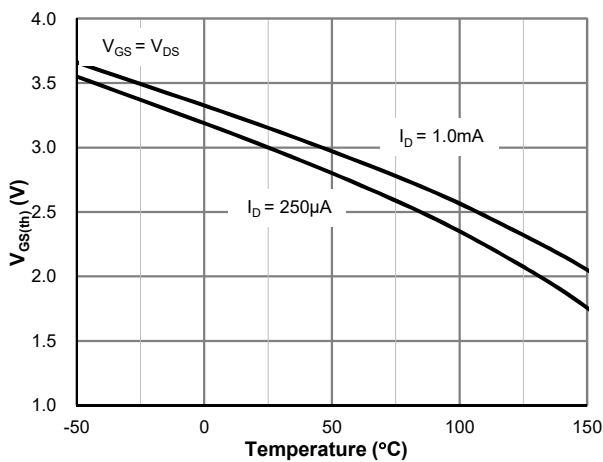
**Figure 2: Transfer Characteristics**



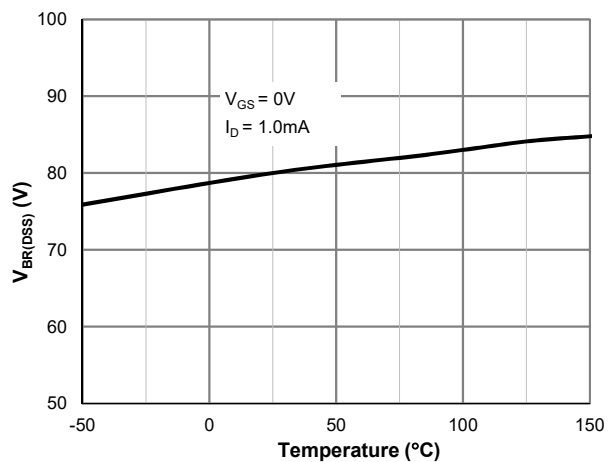
**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**



**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**

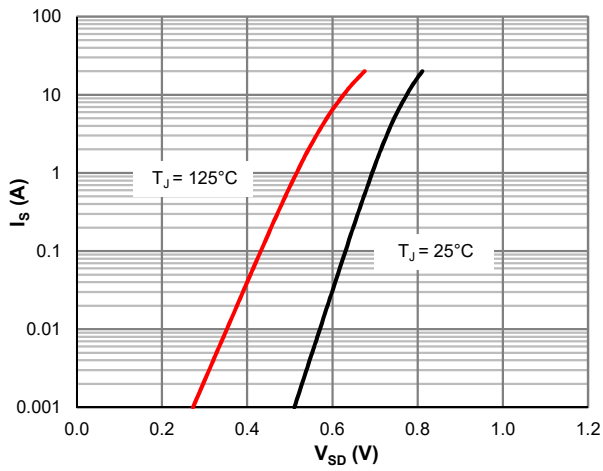


**Figure 5:  $V_{GS(th)}$  vs. Junction Temperature**

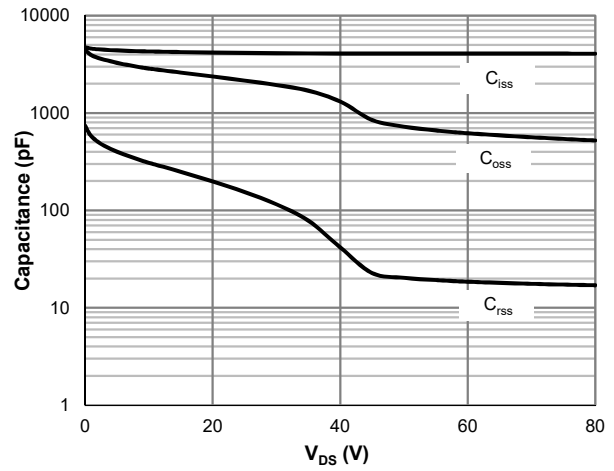


**Figure 6:  $V_{BR(DSS)}$  vs. Junction Temperature**

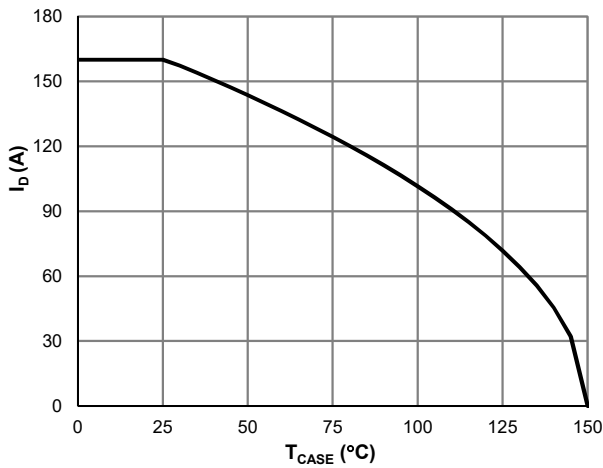
**Typical Electrical & Thermal Characteristics**



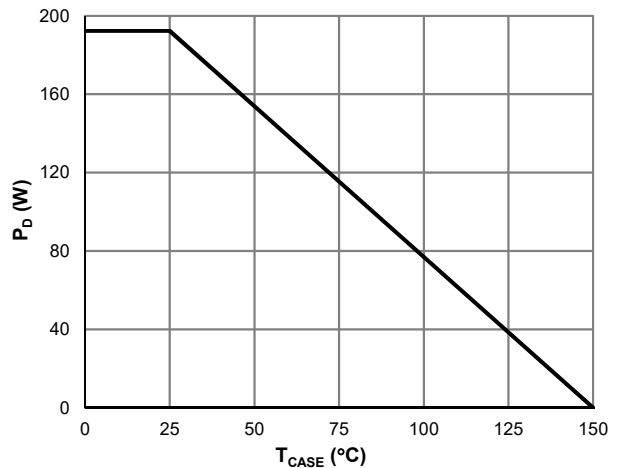
**Figure 7: Body-Diode Characteristics**



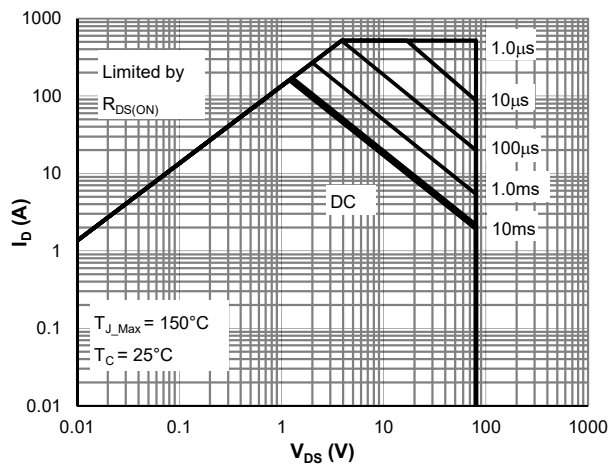
**Figure 8: Capacitance Characteristics**



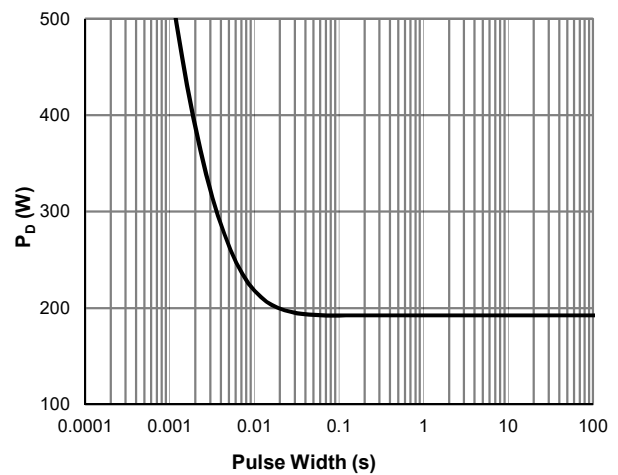
**Figure 9: Current De-rating**



**Figure 10: Power De-rating**



**Figure 11: Maximum Safe Operating Area**



**Figure 12: Single Pulse Power Rating, Junction-to-Case**



### Typical Electrical & Thermal Characteristics

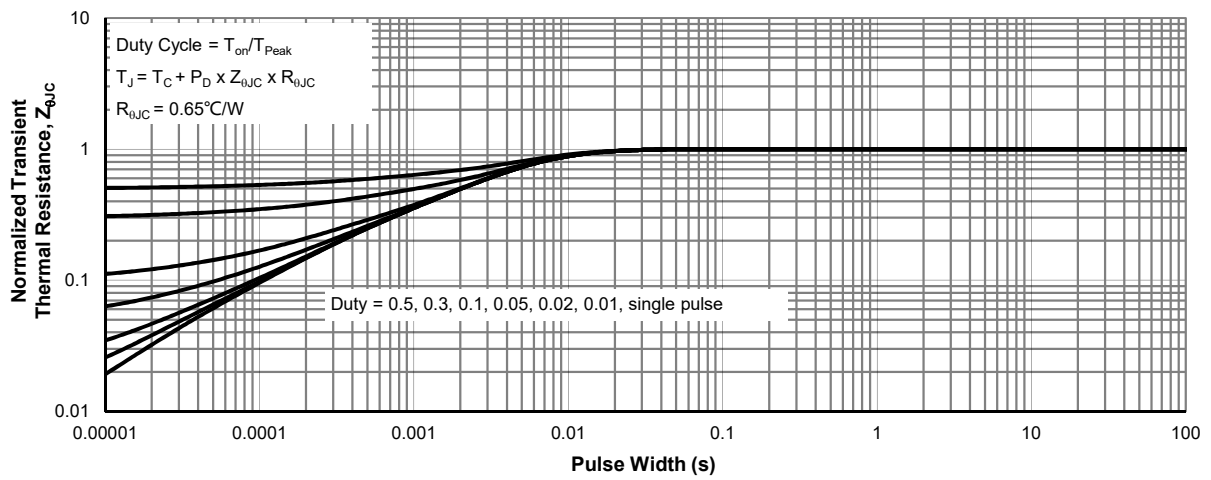
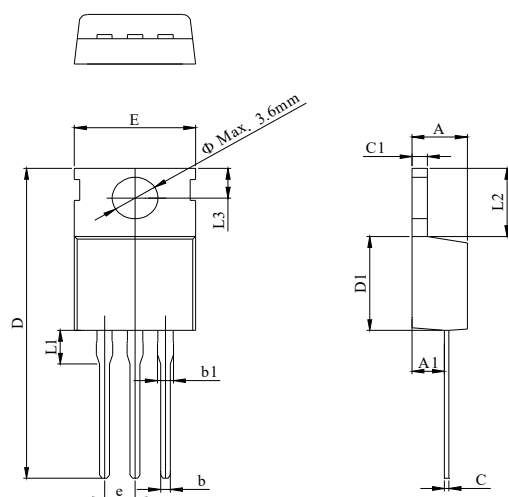


Figure 13: Normalized Maximum Transient Thermal Impedance

### TO-220-3L Package Information

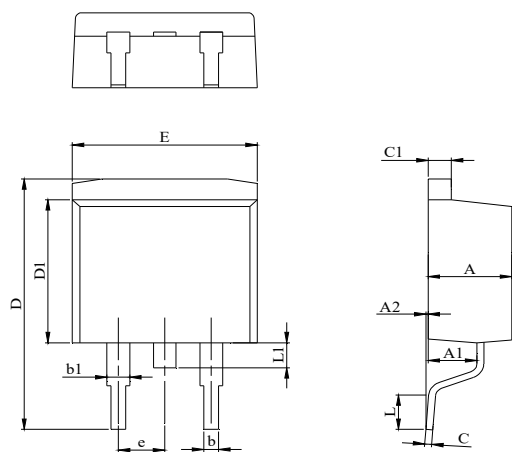
#### Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24		4.70
A1	2.20		3.00
b	0.70		0.95
b1	1.14		1.70
C	0.40		0.60
C1	1.15		1.40
D	28.00		29.80
D1	8.80		9.90
E	9.70		10.50
L1			3.80
L2	6.25		6.90
L3	2.40		3.00
e		2.54 BSC	

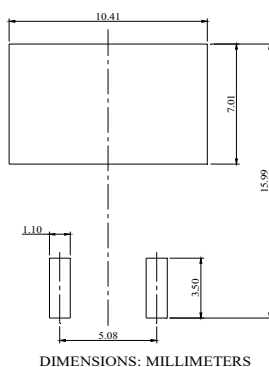
### TO-263-3L Package Information

#### Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24		4.77
A1	2.30		2.89
A2	0.00	0.10	0.25
b	0.70		0.96
b1	1.17		1.70
C	0.30		0.60
C1	1.15		1.42
D	14.10		15.88
D1	8.50		9.60
E	9.78		10.36
L	1.78		2.79
L1			1.75
e		2.54	

#### Recommend Soldering Footprint



单击下面可查看定价，库存，交付和生命周期等信息

[>>JW\(捷捷微\)](#)